



SLP830S / SLF830S

# SLP830S / SLF830S

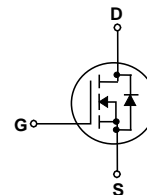
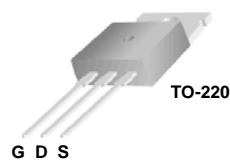
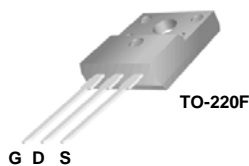
## 500V N-Channel MOSFET

### General Description

This Power MOSFET is produced using Maple semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

### Features

- 5.0A, 500V,  $R_{DS(on)} = 1.35\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 26nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	SLF830S	SLP830S	Units
V <sub>DSS</sub>	Drain-Source Voltage	500		V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	5.0		A
		3.0		A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	20		A
V <sub>GSS</sub>	Gate-Source Voltage	±30		V
EAS	Single Pulsed Avalanche Energy (Note 2)	280		mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	5.0		A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	--		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)	48	74	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150		°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

### Thermal Characteristics

Symbol	Parameter	Max.		Units
		SLF830S	SLP830S	
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	2.60	1.69	°C/W
R <sub>θJS</sub>	Thermal Resistance, Case-to-Sink Typ.	62.5	62.5	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	110	110	°C/W

**Electrical Characteristics**T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	500	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25 °C	--	0.61	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	--	--	25	μA
		V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C	--	--	250	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	--	4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A	--	1.35	1.5	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 2.0 A (Note 4)	2.4	--	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	560	--	pF
C <sub>oss</sub>	Output Capacitance		--	45	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	17	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 5.0 A, R <sub>G</sub> = 25 Ω (Note 4, 5)	--	--	--	ns
t <sub>r</sub>	Turn-On Rise Time		--	--	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	20	--	ns
t <sub>f</sub>	Turn-Off Fall Time		--	--	--	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 4.0A, V <sub>GS</sub> = 10 V (Note 4, 5)	--	13.3	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	4.0	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	15	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	5.0	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	20	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.0 A	--	--	1.6	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.0 A,	--	220	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/us (Note 4)	--	1.0	--	μC

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I<sub>AS</sub> = 5.0A, L=24mH, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 5.0A, di/dt ≤ 200A/us, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

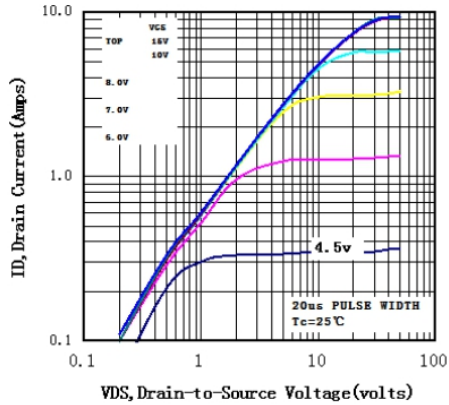


Figure 1. Typical Output Characteristics  
Tc=25°C

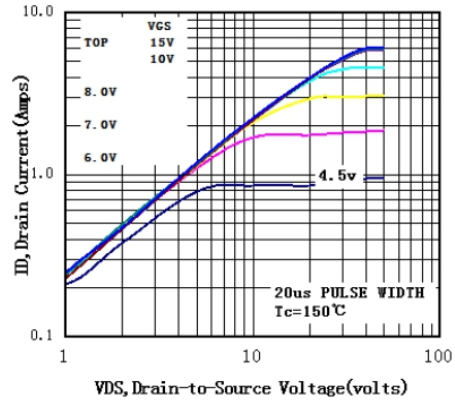


Figure 2. Typical Output Characteristics  
Tc=150°C

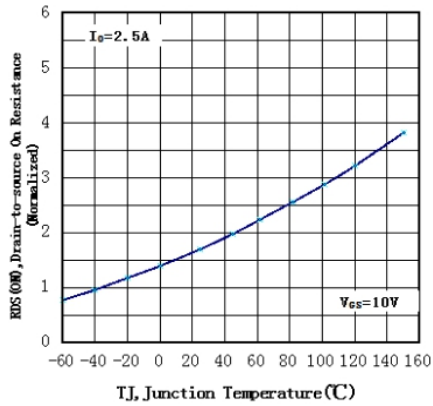


Figure 3. Normalized Resistance VS  
Temperature

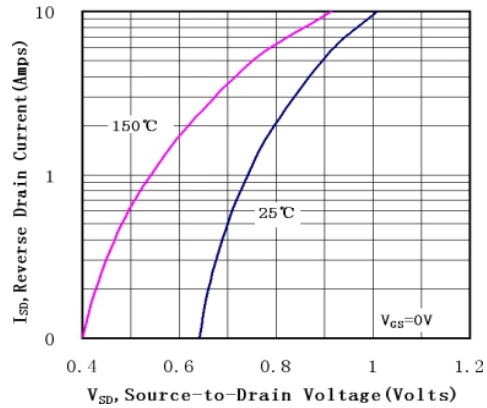


Figure 4. Typical Source-Drain Diode  
Forward Voltage

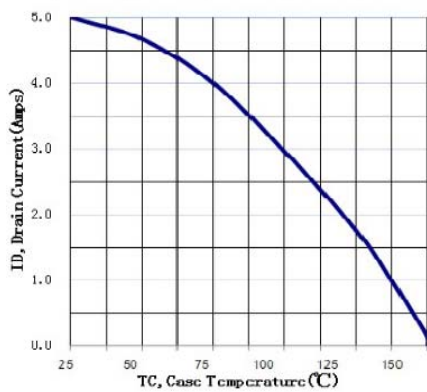


Figure 5. Maximum Current VS  
Case Temperature

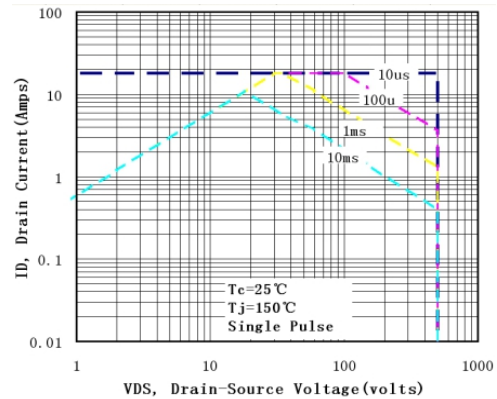
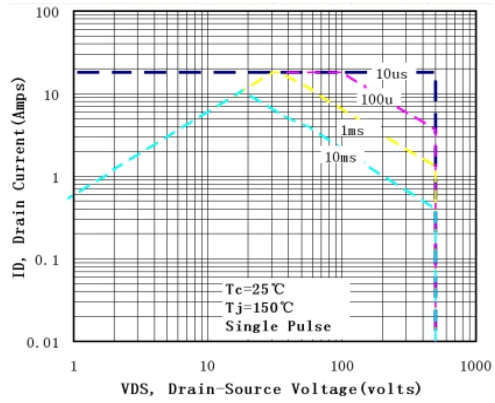


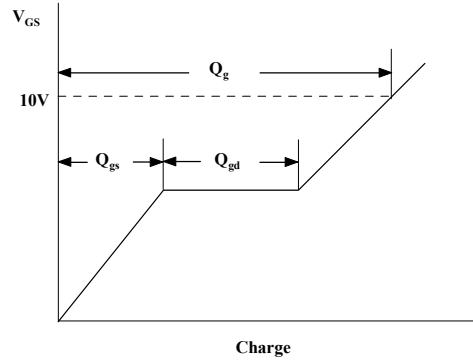
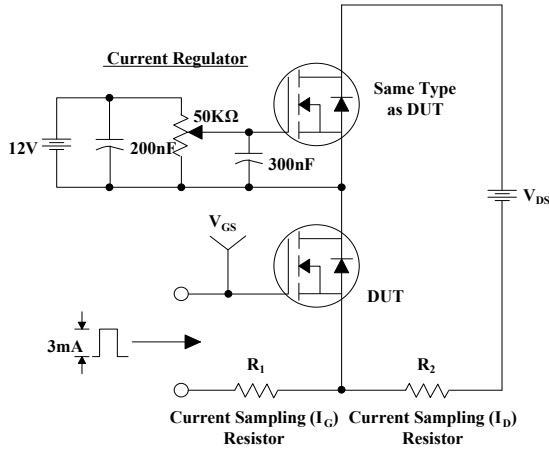
Figure 6-1. Maximum Safe Operating Area  
TO-220F

**Typical Characteristics** (Continued)

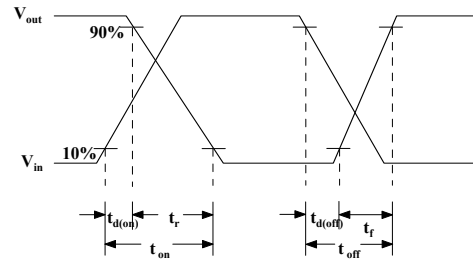
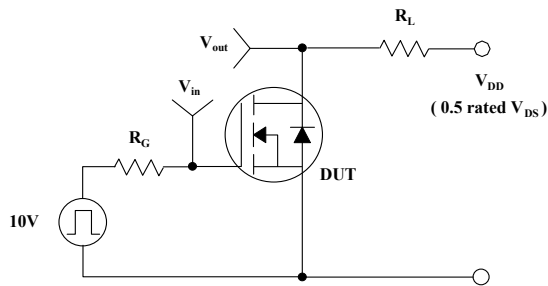


**Figure 6-2. Maximum Safe Operating Area  
TO-220**

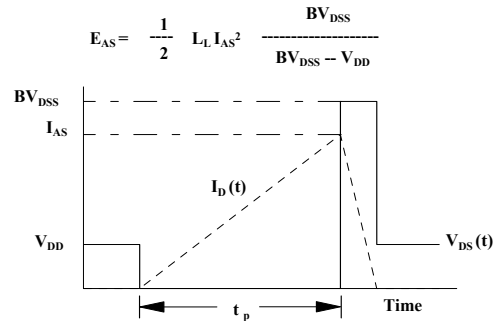
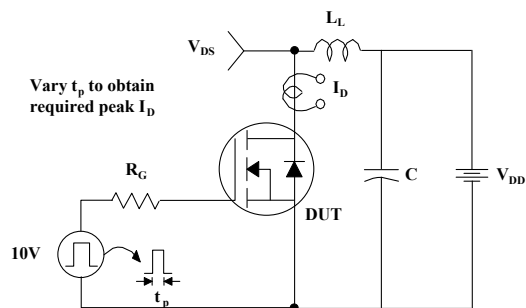
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms



### Peak Diode Recovery dv/dt Test Circuit & Waveforms

